

ATA6566

High-Speed CAN Transceiver with Standby Mode for the Japanese Market – CAN FD Ready

Features

- · Compliant with Japanese OEM Requirements
- Certified According to Latest VeLIO (Vehicle LAN Interoperability and Optimization) Test Specification
- Fully ISO 11898-2, ISO 11898-5, ISO 11898-2: 2016 and SAE J2962-2 Compliant
- · Communication Speed up to 2 Mbit/s
- Low Electromagnetic Emission (EME) and High Electromagnetic Immunity (EMI)
- Differential Receiver with Wide Common-Mode Range
- Remote Wake-up Capability via CAN Bus Wake-up on Pattern (WUP) as Specified in ISO 11898-2: 2016, 3.8 µs Activity Filter Time
- Functional Behavior Predictable under All Supply Conditions
- Transceiver Disengages from the Bus when Not Powered Up
- RXD Recessive Clamping Detection
- High Electrostatic Discharge (ESD) Handling Capability on the Bus Pins
- Bus Pins Protected Against Transients in Automotive Environments
- Transmit Data (TXD) Dominant Time-out Function
- Undervoltage Detection on VCC and VIO Pins
- CANH/CANL Short-Circuit and Overtemperature
 Protected
- Fulfills the OEM "Hardware Requirements for LIN, CAN and FlexRay™ Interfaces in Automotive Applications", Rev. 1.3
- Qualified According to AEC-Q100
- Two Ambient Temperature Grades:
 - ATA6566-GAQW1 and ATA6566-GBQW1 up to T_{amb} = +125°C
 - ATA6566-GAQW0 and ATA6566-GBQW0 up to T_{amb} = +150°C
- Packages: 8-Pin SOIC, 8-Pin VDFN with Wettable Flanks (Moisture Sensitivity Level 1)

Applications

Classical CAN and CAN FD networks in Automotive, Industrial, Aerospace, Medical and Consumer applications.

General Description

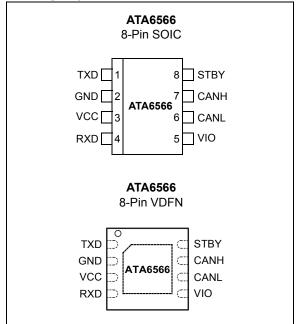
The ATA6566 is a high-speed CAN transceiver that provides an interface between a Controller Area Network (CAN) protocol controller and the physical two-wire CAN bus. The transceiver is designed for high-speed (up to 2 Mbit/s) CAN applications in the automotive industry, providing differential transmit and receive capability to (a microcontroller with) a CAN protocol controller.

It offers improved Electromagnetic Compatibility (EMC) and Electrostatic Discharge (ESD) performance, as well as features such as:

- Ideal passive behavior to the CAN bus when the supply voltage is off
- Direct interfacing to microcontrollers with supply voltages from 3V to 5V

Two operating modes, together with the dedicated fail-safe features, make the ATA6566 an excellent choice for all types of high-speed CAN networks, especially in nodes requiring Low-Power mode with wake-up capability via the CAN bus.

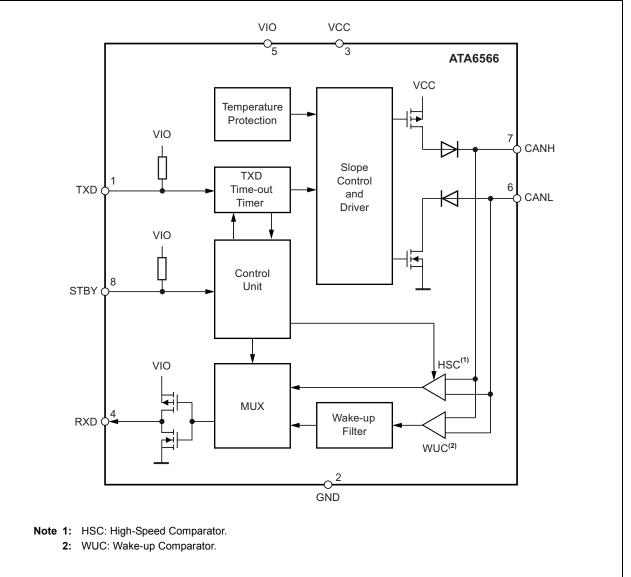
Package Types



ATA6566 Family Members

Device	Grade 0	Grade 1	VDFN8	SOIC8	Description
ATA6566-GAQW0	X			Х	Standby mode, VIO – pin for compatibility with 3.3V and 5V microcontroller
ATA6566-GBQW0	X		Х		Standby mode, VIO – pin for compatibility with 3.3V and 5V microcontroller
ATA6566-GAQW1		Х		Х	Standby mode, VIO – pin for compatibility with 3.3V and 5V microcontroller
ATA6566-GBQW1		Х	Х		Standby mode, VIO – pin for compatibility with 3.3V and 5V microcontroller

Functional Block Diagram



1.0 FUNCTIONAL DESCRIPTION

The ATA6566 is a stand-alone, high-speed CAN transceiver, compliant with the ISO 11898-2, ISO 11898-2: 2016, ISO 11898-5 and SAE J2962-2 CAN standards. It provides a very low current consumption in Standby mode and wake-up capability via the CAN bus. Pin 5 is the VIO pin and should be connected to the microcontroller supply voltage. This allows direct interfacing to microcontrollers with supply voltages down

to 3V, and adjusts the signal levels of the TXD, RXD and STBY pins to the I/O levels of the microcontroller. The I/O ports are supplied by the VIO pin.

1.1 Operating Modes

The ATA6566 supports two operating modes: Silent and Normal. These modes can be selected via the STBY pin. See Figure 1-1 and Table 1-1 for a description of the operating modes.

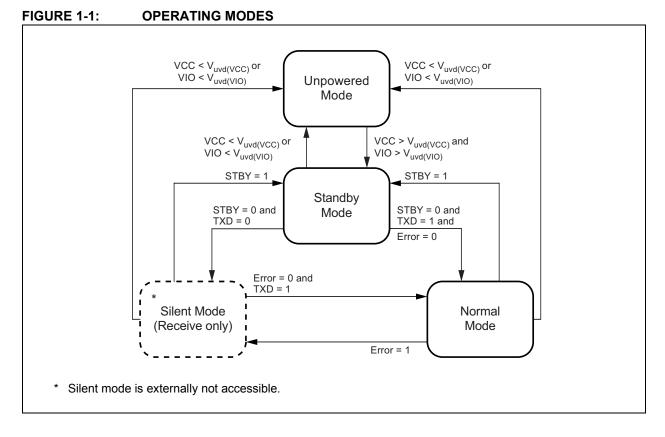


TABLE 1-1:OPERATING MODES

Mode	Inp	uts	Outputs		
wode	STBY	Pin TXD	CAN Driver	Pin RXD	
Unpowered	X ⁽¹⁾	X ⁽¹⁾	Recessive	Recessive	
Standby	High	X ⁽¹⁾	Recessive	Active ⁽²⁾	
Normal	Low	Low	Dominant	Low	
	Low	High	Recessive	High	

Note 1: Irrelevant.

2: Reflects the bus only for wake-up.

1.1.1 NORMAL MODE

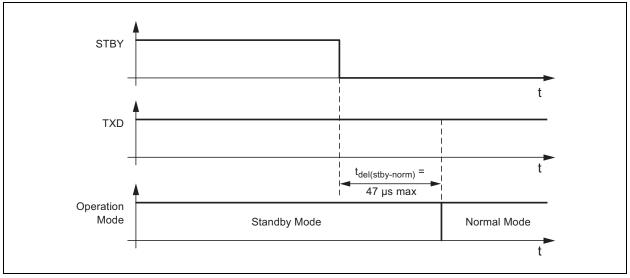
A low level on the STBY pin, together with a high level on the TXD pin, selects the Normal mode. In this mode, the transceiver is able to transmit and receive data via the CANH and CANL bus lines (see the "Functional Block Diagram"). The output driver stage is active and drives data from the TXD input to the CAN bus. The High-Speed Comparator (HSC) converts the analog data on the bus lines into digital data, which is output to pin RXD. The bus biasing is set to $V_{VCC}/2$ and the undervoltage monitoring of VCC is active.

The slope of the output signals on the bus lines is controlled and optimized to ensure the lowest possible Electromagnetic Emission (EME).

To switch the device to Normal Operating mode, set the STBY pin to low and the TXD pin to high (see Table 1-1 and Figure 1-2). The STBY and TXD pins each provide a pull-up resistor to VIO, ensuring defined levels if the pins are open.

Please note that the device cannot enter Normal mode as long as TXD is at ground level.

FIGURE 1-2: SWITCHING FROM STANDBY MODE TO NORMAL MODE



1.1.2 STANDBY MODE

A high level on the STBY pin selects Standby mode. In this mode, the transceiver is not able to transmit or correctly receive data via the bus lines. The transmitter and the High-Speed Comparator (HSC) are switched off to reduce current consumption.

1.1.3 REMOTE WAKE-UP VIA THE CAN BUS

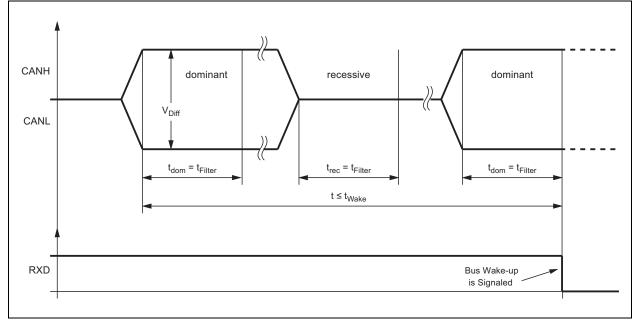
In Standby mode, the bus lines are biased to ground to reduce current consumption to a minimum. The ATA6566 monitors the bus lines for a valid wake-up pattern, as specified in the ISO 11898-2: 2016. This filtering helps to avoid spurious wake-up events that would be triggered by scenarios, such as a dominant clamped bus or by a dominant phase due to noise, spikes on the bus, automotive transients or EMI. The wake-up pattern consists of at least two consecutive dominant bus levels for a duration of at least t_{Filter}, each separated by a recessive bus level with a duration of at

least t_{Filter} . Dominant or recessive bus levels shorter than t_{Filter} are always ignored. The complete dominant-recessive-dominant pattern, as shown in Figure 1-3, must be received within the bus wake-up time-out time, t_{Wake} , to be recognized as a valid wake-up pattern. Otherwise, the internal wake-up logic is reset and then the complete wake-up pattern must be retransmitted to trigger a wake-up event. The RXD pin remains at a high level until a valid wake-up event has been detected.

During normal mode, at a VCC or VIO undervoltage condition or when the complete wake-up pattern is not received within t_{Wake} , no wake-up is signaled at the RXD pin.

When a valid CAN wake-up pattern is detected on the bus, the RXD pin switches to low to signal a wake-up request. A transition to Normal mode is not triggered until the STBY pin is forced back to low by the microcontroller.





1.2 Fail-Safe Features

1.2.1 TXD DOMINANT TIME-OUT FUNCTION

A TXD dominant time-out timer is started when the TXD pin is set to low. If the low state on the TXD pin persists for longer than $t_{to(dom)TXD}$, the transmitter is disabled, releasing the bus lines to a recessive state. This function prevents a hardware and/or software application failure from driving the bus lines to a permanent dominant state (blocking all network communications). The TXD dominant time-out timer is reset when the TXD pin is set to high. If the low state on the TXD pin is longer than $t_{to(dom)TXD}$, then the TXD pin has to be set to high \geq 4 µs in order to reset the TXD dominant time-out timer.

1.2.2 INTERNAL PULL-UP STRUCTURE AT THE TXD AND STBY INPUT PINS

The TXD and STBY pins have an internal pull-up to VIO. This ensures a safe, defined state in case one or all of these pins are left floating. Pull-up currents flow in these pins in all states, meaning all pins should be in a high state during Standby mode to minimize the current consumption.

1.2.3 UNDERVOLTAGE DETECTION ON PINS VCC AND VIO

If V_{VCC} or V_{VIO} drops below its respective undervoltage detection levels ($V_{uvd(VCC)}$ and $V_{uvd(VIO)}$, see Section 2.0 "Electrical Characteristics"), the transceiver switches off and disengages from the bus until V_{VCC} and V_{VIO} have recovered. The low-power Wake-up Comparator is only

switched off during a VCC or VIO undervoltage. The logic state of the STBY pin is ignored until the VCC voltage or the VIO voltage has recovered.

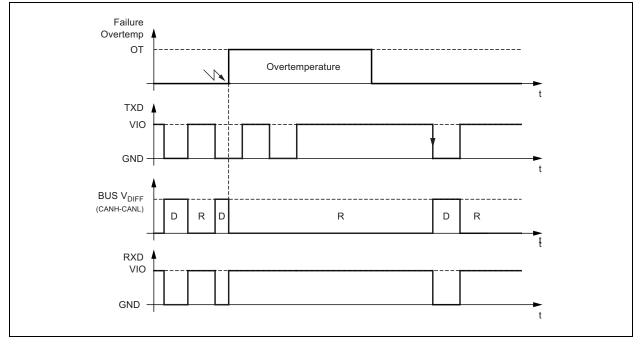
1.2.4 BUS WAKE-UP ONLY AT DEDICATED WAKE-UP PATTERN

Due to the implementation of the wake-up filtering, the ATA6566 does not wake-up when the bus is in a long dominant phase; it only wakes up at a dedicated wake-up pattern as specified in the ISO 11898-2: 2016. This means for a valid wake-up, at least two consecutive dominant bus levels for a duration of at least t_{Eilter}, each separated by a recessive bus level with a duration of at least t_{Filter}, must be received via the bus. Dominant or recessive bus levels shorter than t_{Filter} are always ignored. The complete dominant-recessive-dominant pattern, as shown in Figure 1-3, must be received within the bus wake-up time-out time, t_{Wake}, to be recognized as a valid wake-up pattern. This filtering leads to a higher robustness against EMI and transients, and therefore, significantly reduces the risk of an unwanted bus wake-up.

1.2.5 OVERTEMPERATURE PROTECTION

The output drivers are protected against overtemperature conditions. If the junction temperature exceeds the shutdown junction temperature, T_{Jsd} , the output drivers are disabled until the junction temperature drops below T_{Jsd} and pin TXD is at a high level again. The TXD condition ensures that output driver oscillations due to temperature drift are avoided.

FIGURE 1-4: RELEASE OF TRANSMISSION AFTER OVERTEMPERATURE CONDITION



1.2.6 SHORT-CIRCUIT PROTECTION OF THE BUS PINS

The CANH and CANL bus outputs are short-circuit protected, either against GND or a positive supply voltage. A current-limiting circuit protects the transceiver against damage. If the device is heating up due to a continuous short on CANH or CANL, the internal overtemperature protection switches the bus transmitter off.

1.2.7 **RXD RECESSIVE CLAMPING**

This fail-safe feature prevents the controller from sending data on the bus if its RXD line is clamped to high (e.g., recessive). That is, if the RXD pin cannot signalize a dominant bus condition (e.g., because it is shorted to VCC), the transmitter within ATA6566 is disabled to avoid possible data collisions on the bus. In Normal mode, the device permanently compares the state of the High-Speed Comparator (HSC) with the state of the RXD pin. If the HSC indicates a dominant bus state for more than $t_{RC det}$, without the RXD pin doing the same, a recessive clamping situation is detected and the device is forced into Silent mode (receive only). This Fail-Safe mode is released by either entering Standby or Unpowered mode, or if the RXD pin is showing a dominant (e.g., low) level again.

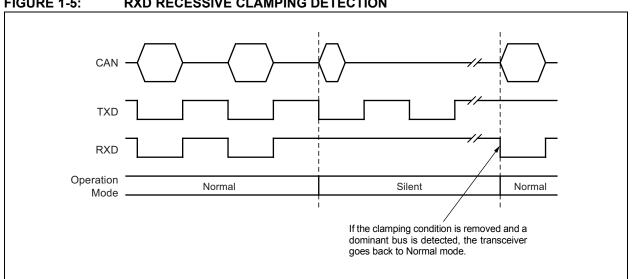


FIGURE 1-5: **RXD RECESSIVE CLAMPING DETECTION**

1.3 Pin Descriptions

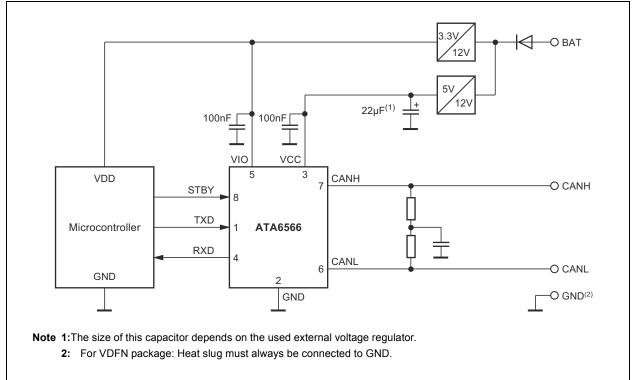
The descriptions of the pins are listed in Table 1-2.

Pin Name	Description
TXD	Transmit Data Input
GND	Ground Supply
VCC	Supply Voltage
RXD	Receive Data Output; Reads Out Data from the Bus Lines
VIO	Supply Voltage for I/O Level Adapter
CANL	Low-Level CAN Bus Line
CANH	High-Level CAN Bus Line
STBY	Standby Mode Control Input
EP ⁽¹⁾	Exposed Thermal Pad: Heat Slug, Internally Connected to the GND Pin
	TXD GND VCC RXD VIO CANL CANH STBY

TABLE 1-2: PIN FUNCTION TABLE

Note 1: Only for the VDFN package.

Typical Application



2.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings^(†)

DC Voltage at CANH and CANL	27V to +42V
Transient Voltage on CANH and CANL (ISO 7637, Part 2)	-150V to +100V
Maximum Differential Bus Voltage	–5V to +18V
DC Voltage on All Other Pins	–0.3V to +5.5V
ESD Protection on CANH and CANL Pins (IEC 61000-4-2)	±8 kV
ESD (HBM following STM 5.1 with 1.5 k Ω /100 pF) – Pins CANH, CANL to GND	±6 kV
Component Level ESD (HBM according to ANSI/ESD STM 5.1), JESD22-A114, AEC-Q 100 (002)	±4 kV
CDM ESD STM 5.3.1	±750V
ESD Machine Model AEC-Q100-RevF(003)	±200V
Virtual Junction Temperature (T _{vJ})	–40°C to +175°C
Storage Temperature (T _{stg})	–55°C to +150°C

† Notice: Stresses beyond those listed below may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TABLE 2-1: ELECTRICAL CHARACTERISTICS

Electrical Specifications: Grade 1: $T_{amb} = -40^{\circ}C$ to +125°C; Grade 0: $T_{amb} = -40^{\circ}C$ to +150°C; $T_{vJ} \le 170^{\circ}C$; $V_{VCC} = 4.75V$ to 5.25V; $V_{VIO} = 2.8V$ to 5.5V; $R_L = 60\Omega$, $C_L = 100$ pF unless otherwise specified. All voltages are defined in relation to ground; positive currents flow into the IC.

defined in relation to ground;						[
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
Supply, Pin VCC						
Supply Voltage	V _{VCC}	4.75	—	5.25	V	
Supply Current in Normal	I _{VCC_rec}	2	—	5	mA	Recessive, $V_{TXD} = V_{VIO}$
Mode	I _{VCC_dom}	30	50	70	mA	Dominant, V _{TXD} = 0V
	I _{VCC_short}	—	_	85	mA	Short between CANH and CANL (Note 1)
Supply Current in Standby	IVCC_STBY	—	_	12	μA	$V_{VCC} = V_{VIO}, V_{TXD} = V_{VIO}$
Mode	IVCC_STBY	_	7	_	μA	T _{amb} = +25°C (Note 3)
Undervoltage Detection Threshold on Pin VCC	V _{uvd(VCC)}	2.75	_	4.5	V	
I/O Level Adapter Supply, F	in VIO					
Supply Voltage on Pin VIO	V _{VIO}	2.8		5.5	V	
Supply Current on Pin VIO	I _{VIO_rec}	10	80	250	μA	Normal mode recessive, V _{TXD} = V _{VIO}
	I _{VIO_dom}	50	350	500	μA	Normal mode dominant, V _{TXD} = 0V
	IVIO_STBY	—	_	1	μA	Standby mode
Undervoltage Detection Threshold on Pin VIO	V _{uvd(VIO)}	1.3	—	2.7	V	
Mode Control Input, Pin ST	BY					
High-Level Input Voltage	VIH	$0.7\times V_{VIO}$	_	V _{VIO} + 0.3	V	
Low-Level Input Voltage	V _{IL}	-0.3	—	$0.3 \times V_{VIO}$	V	
Pull-up Resistor to VIO	R _{pu}	75	125	175	kΩ	V _{STBY} = 0V
Low-Level Leakage Current	١L	-2	_	+2	μA	V _{STBY} = V _{VIO}
CAN Transmit Data Input, F	Pin TXD					
High-Level Input Voltage	VIH	$0.7\times V_{VIO}$	_	V _{VIO} + 0.3	V	
Low-Level Input Voltage	V _{IL}	-0.3		$0.3 \times V_{VIO}$	V	
Pull-up Resistor to VIO	R _{TXD}	20	35	50	kΩ	V _{TXD} = 0V
High-Level Leakage Current	I _{TDX}	-2	—	+2	μA	Normal mode, $V_{TXD} = V_{VIO}$
Input Capacitance	C _{TXD}	—	5	10	pF	(Note 3)
CAN Receive Data Output,	Pin RXD			T	I	
High-Level Output Current	I _{ОН}	-8	_	-1	mA	Normal mode, $V_{RXD} = V_{VIO} - 0.4V$, $V_{VIO} = V_{VCC}$
Low-Level Output Current	I _{OL}	2	_	12	mA	Normal mode, V _{RXD} = 0.4V, bus dominant
Bus Lines, Pins CANH and	CANL					
Single-Ended Dominant Output Voltage	V _{O(dom)}	2.75	3.5	4.5	V	V_{TXD} = 0V, t < t _{to(dom)TXD} , R _L = 50 Ω to 65 Ω , CANH pin
Note 1: Type B: 100% cor		0.5	3.5 1.5	4.5 2.25	V V	CANH pin CANL pin (Note 1)

Note 1: Type B: 100% correlation tested.

2: Type C: Characterized on samples.

3: Type D: Design parameter.

TABLE 2-1: ELECTRICAL CHARACTERISTICS (CONTINUED)

Electrical Specifications: Grade 1: $T_{amb} = -40^{\circ}C$ to +125°C; Grade 0: $T_{amb} = -40^{\circ}C$ to +150°C; $T_{vJ} \le 170^{\circ}C$; $V_{VCC} = 4.75V$ to 5.25V; $V_{VIO} = 2.8V$ to 5.5V; $R_L = 60\Omega$, $C_L = 100$ pF unless otherwise specified. All voltages are defined in relation to ground; positive currents flow into the IC.

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
Transmitter Voltage Symmetry	V _{Sym}	0.9	1	1.1	-	V _{Sym} = (V _{CANH} + V _{CANL})/V _{VCC} (Note 3)
Bus Differential Output Voltage	V _{Diff}	1.5	—	3	V	V_{TXD} = 0V, t < t _{to(dom)TXD} , R _L = 45 Ω to 65 Ω
		1.5	—	3.3	V	V_{TXD} = 0V, t < t _{to(dom)TXD} , R _L = 70 Ω (Note 3)
		1.5	—	5	V	$V_{TXD} = 0V, t < t_{to(dom)TXD,}$ R _L = 2240 Ω (Note 3)
		-50	—	+50	mV	V_{VCC} = 4.75V to 5.25V, V_{TXD} = V_{VIO} , receive, no load
Recessive Output Voltage	V _{O(rec)}	2	$0.5 \times V_{VCC}$	3	V	Normal mode, V _{TXD} = V _{VIO} , no load
	V _{O(rec)}	-0.1	-	+0.1	V	Standby mode, V _{TXD} = V _{VIO} , no load
Differential Receiver Threshold Voltage	V _{th(RX)dif}	0.5	0.7	0.9	V	Normal mode, V _{cm(CAN)} = –27V to +27V
	V _{th(RX)dif}	0.4	0.7	1.1	V	Standby mode, V _{cm(CAN)} = -27V to +27V (Note 1)
Differential Receiver Hysteresis Voltage (HSC)	V _{hys(RX)} dif	50	120	200	mV	Normal mode, V _{cm(CAN)} = –27V to +27V
Differential Receiver Threshold Voltage at Recessive to Dominant Transition	V _{th(RX)dif_rec} _dom	0.7	0.8	0.9	V	Normal mode, V _{cm(CAN)} = -2V to +7V (Note 1)
Dominant Output Current	I _{IO(dom)}					V_{TXD} = 0V, t < t _{to(dom)TXD} , V _{VCC} = 5V,
		-75 35	—	–35 75	mA mA	CANH pin, $V_{CANH} = -5V$ CANL pin, $V_{CANL} = +40V$
Recessive Output Current	I _{IO(rec)}	-5	_	+5	mA	Normal mode, $V_{TXD} = V_{VIO}$, no load, $V_{CANH} = V_{CANL} = -27V$ to +32V
Leakage Current	I _{IO(leak)}	-5	0	+5	μA	$V_{VCC} = V_{VIO} = 0V,$ $V_{CANH} = V_{CANL} = 5V$
	I _{IO(leak)}	-5	0	+5	μA	VCC = VIO, connected to GND with $47k\Omega$, V _{CANH} = V _{CANL} = 5V (Note 3)
Input Resistance	R _i	9	15	28	kΩ	V _{CANH} = V _{CANL} = 4V
	R _i	9	15	28	kΩ	–2V ≤ V _{CANH} ≤ +7V, –2V ≤ V _{CANL} ≤ +7V (Note 3)

Note 1: Type B: 100% correlation tested.

- **2:** Type C: Characterized on samples.
- 3: Type D: Design parameter.

TABLE 2-1: ELECTRICAL CHARACTERISTICS (CONTINUED)

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Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
Input Resistance Deviation	ΔR _i	-1	0	+1	%	Between CANH and CANL, $V_{CANH} = V_{CANL} = 4V$
	ΔR _i	-1	0	+1	%	–2V ≤ V _{CANH} ≤ +7V, –2V ≤ V _{CANL} ≤ +7V (Note 3)
Differential Input Resistance	R _{i(dif)}	18	30	56	kΩ	V _{CANH} = V _{CANL} = 4V
	R _{i(dif)}	18	30	56	kΩ	–2V ≤ V _{CANH} ≤ +7V, –2V ≤ V _{CANL} ≤ +7V (Note 3)
Common-Mode Input Capacitance	C _{i(cm)}	_	—	20	pF	f = 500 kHz, CANH and CANL referred to GND (Note 3)
Differential Input Capacitance	C _{i(dif)}	—	—	10	pF	f = 500 kHz, between CANH and CANL (Note 3)
Differential Bus Voltage Range for Recessive State Detection	V _{Diff_rec}	-3	_	+0.5	V	Normal and Silent mode (HSC) (Note 3), $-27V \le V_{CANH} \le +27V$, $-27V \le V_{CANL} \le +27V$
		-3		+0.4	V	Standby mode (WUC), (Note 3), $-27V \le V_{CANH} \le +27V$, $-27V \le V_{CANL} \le +27V$
Differential Bus Voltage Range for Dominant State Detection	V _{Diff_dom}	0.9	_	8	V	Normal and Silent mode (HSC) (Note 3), $-27V \le V_{CANH} \le +27V$, $-27V \le V_{CANL} \le +27V$
		1.15	_	8	V	Normal and Silent mode (WUC) (Note 3), $-27V \le V_{CANH} \le +27V$, $-27V \le V_{CANL} \le +27V$
Transceiver Timing, Pins C	ANH, CANL, T	XD and RX	D (see <mark>Figu</mark>	re 2-1 and	Figure 2	2-2)
Delay Time from TXD to Bus Dominant	$t_{d(TXD-busdom)}$	—	—	140	ns	Normal mode
Delay Time from TXD to Bus Recessive	t _{d(TXD-busrec)}	—	—	140	ns	Normal mode
Delay Time from Bus Dominant to RXD	t _{d(busdom-RXD)}	_	—	140	ns	Normal mode
Delay Time from Bus Recessive to RXD	t _{d(busrec-RXD)}	—	—	140	ns	Normal mode
Propagation Delay from TXD to RXD	t _{PD(TXD-RXD)}			255		Normal mode, $R_L = 60\Omega$, $C_L = 100 \text{ pF}$ Rising edge at pin TXD
		_		255 255	ns ns	Falling edge at pin TXD
TXD Dominant Time-out Time	t _{to(dom)} TXD	0.8	-	3	ms	V _{TXD} = 0V, Normal mode
Bus Wake-up Time-out Time	t _{Wake}	0.8	—	3	ms	Standby mode
Min. Dominant/Recessive Bus Wake-up Time	t _{Filter}	0.5	—	3.8	μs	Standby mode

Note 1: Type B: 100% correlation tested.

2: Type C: Characterized on samples.

3: Type D: Design parameter.

TABLE 2-1: ELECTRICAL CHARACTERISTICS (CONTINUED)

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Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
Delay Time for Standby Mode to Normal Mode Transition	t _{del(stby-norm)}	_	_	47	μs	Falling edge at pin STBY
Delay Time for Normal Mode to Standby Mode Transition	t _{del(norm-stby)}	_		5	μs	Rising edge at pin STBY (Note 3)
Debouncing Time for Recessive Clamping State Detection	t _{RC_det}	_	90	_	ns	V _(CANH-CANL) > 900 mV, RXD = High (Note 3)
Transceiver Timing for Hig External Capacitor on the F			, CANL, TXI) and RXD	(see <mark>Fi</mark>	gure 2-1 and Figure 2-3),
Recessive Bit Time on Pin RXD	t _{Bit(RXD)}	400	_	550	ns	Normal mode, $t_{Bit(TXD)} = 500 \text{ ns}$ $R_L = 60\Omega$, $C_L = 100 \text{ pF}$
Recessive Bit Time on the Bus	t _{Bit(Bus)}	435	_	530	ns	Normal mode, $t_{Bit(TXD)} = 500 \text{ ns}$ $R_L = 60\Omega$, $C_L = 100 \text{ pF}$
Receiver Timing Symmetry	Δt_{Rec}	-65	_	+40	ns	Normal mode, $t_{Bit(TXD)} = 500 \text{ ns},$ $\Delta t_{Rec} = t_{Bit(RXD)} - t_{Bit(Bus)}$ $R_L = 60\Omega, C_L = 100 \text{ pF}$

Note 1: Type B: 100% correlation tested.

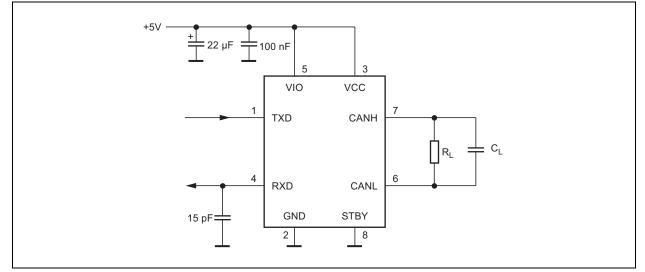
2: Type C: Characterized on samples.

3: Type D: Design parameter.

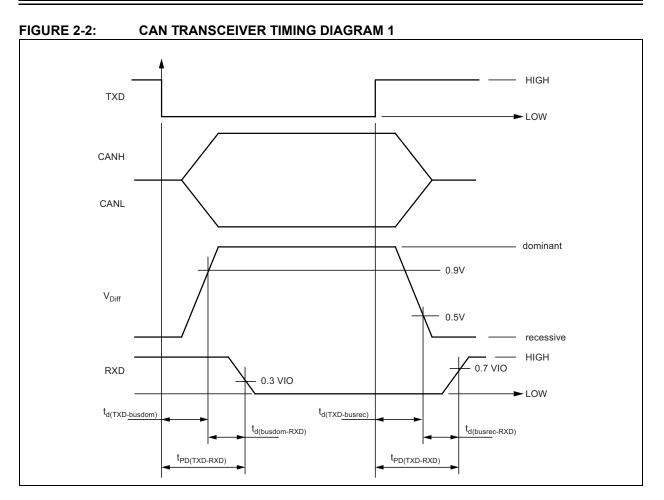
TABLE 2-2: TEMPERATURE SPECIFICATIONS

Demonsterne	0	Min	True	Maria	11	O a malifi a ma
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
8-Lead SOIC					-	
Thermal Resistance Virtual Junction to Ambient	R _{thvJA}	—	145		K/W	
Thermal Shutdown of the Bus Drivers for ATA6566-GAQW1 (Grade 1)	T _{vJsd}	150	_	195	°C	
Thermal Shutdown of the Bus Drivers for ATA6566-GAQW0 (Grade 0)	T _{vJsd}	170	_	195	°C	
Thermal Shutdown Hysteresis	T _{vJsd_hys}	—	15	—	°C	
8-Lead VDFN	·					
Thermal Resistance Virtual Junction to Heat Slug	R _{thvJC}	_	10	_	K/W	
Thermal Resistance Virtual Junction to Ambient, where Heat Slug is Soldered to PCB according to JEDEC	R _{thvJA}	_	50	—	K/W	
Thermal Shutdown of the Bus Drivers for ATA6566-GBQW1 (Grade 1)	T _{vJsd}	150	—	195	°C	
Thermal Shutdown of the Bus drivers for ATA6566-GBQW0 (Grade 0)	T _{vJsd}	170	—	195	°C	
Thermal Shutdown Hysteresis	T _{vJsd_hys}	_	15		°C	

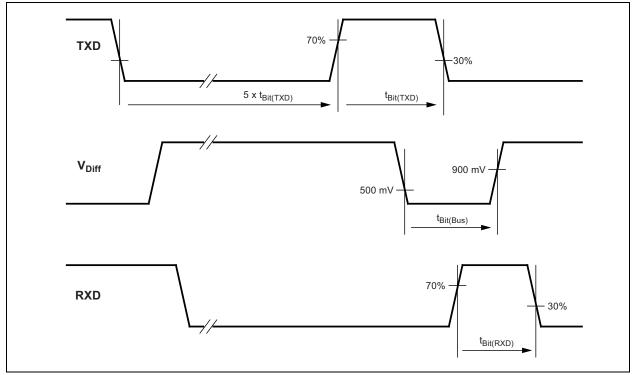
FIGURE 2-1: TIMING TEST CIRCUIT FOR THE ATA6566 CAN TRANSCEIVER



ATA6566

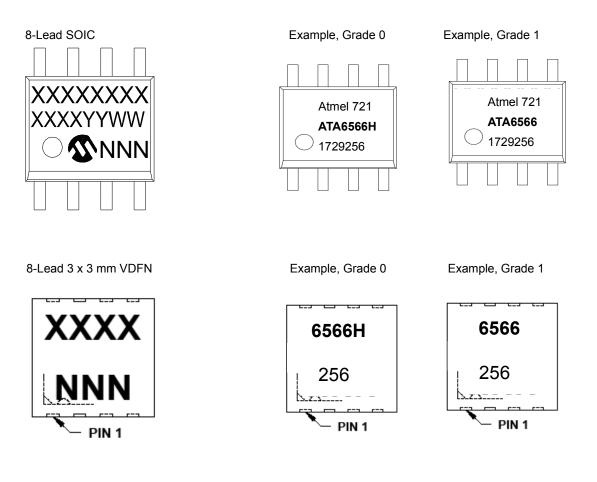




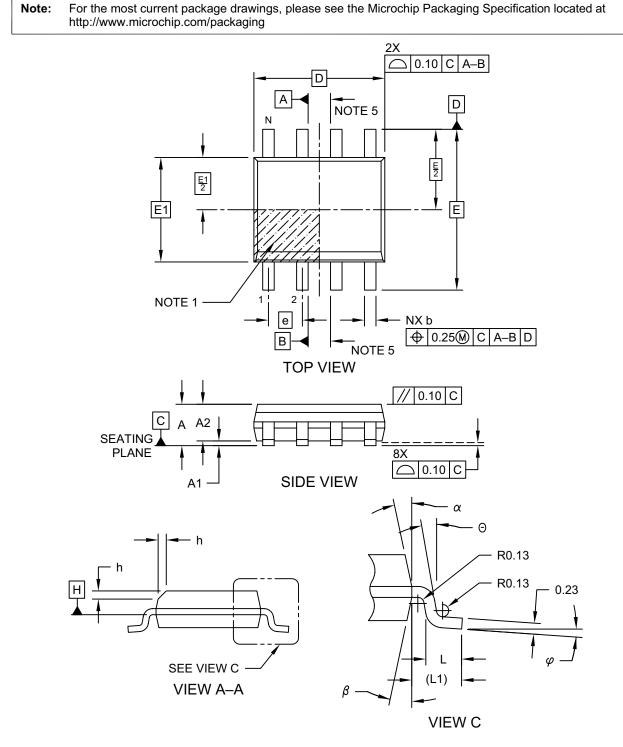


3.0 PACKAGING INFORMATION

3.1 Package Marking Information



Legend	: XXX Y YY WW NNN (©3) *	Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.
	be carried	nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available s for customer-specific information.

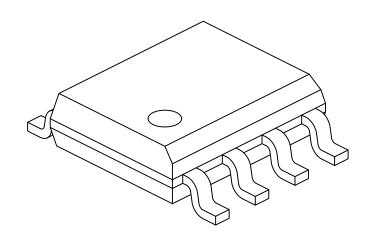


8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm (.150 In.) Body [SOIC]

Microchip Technology Drawing No. C04-057-SN Rev D Sheet 1 of 2

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm (.150 In.) Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS				
Dimension	MIN	NOM	MAX		
Number of Pins	N		8		
Pitch	е		1.27 BSC		
Overall Height	Α	-	-	1.75	
Molded Package Thickness	A2	1.25	-	-	
Standoff §	A1	0.10	-	0.25	
Overall Width	E	6.00 BSC			
Molded Package Width	E1	3.90 BSC			
Overall Length	D	4.90 BSC			
Chamfer (Optional)	h	0.25	-	0.50	
Foot Length	L	0.40	-	1.27	
Footprint	L1		1.04 REF		
Foot Angle	φ	0°	-	8°	
Lead Thickness	С	0.17	-	0.25	
Lead Width	b	0.31	-	0.51	
Mold Draft Angle Top	α	5°	-	15°	
Mold Draft Angle Bottom	β	5°	-	15°	

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. § Significant Characteristic

- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

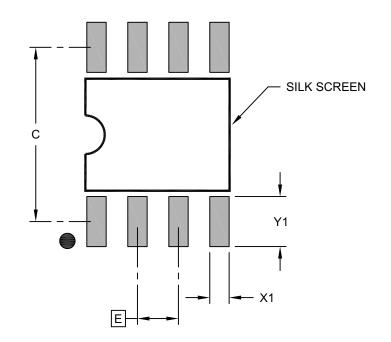
REF: Reference Dimension, usually without tolerance, for information purposes only.

5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-057-SN Rev D Sheet 2 of 2

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	MILLIMETERS			
Dimension	MIN	NOM	MAX	
Contact Pitch	E	1.27 BSC		
Contact Pad Spacing	С		5.40	
Contact Pad Width (X8)	X1			0.60
Contact Pad Length (X8)	Y1			1.55

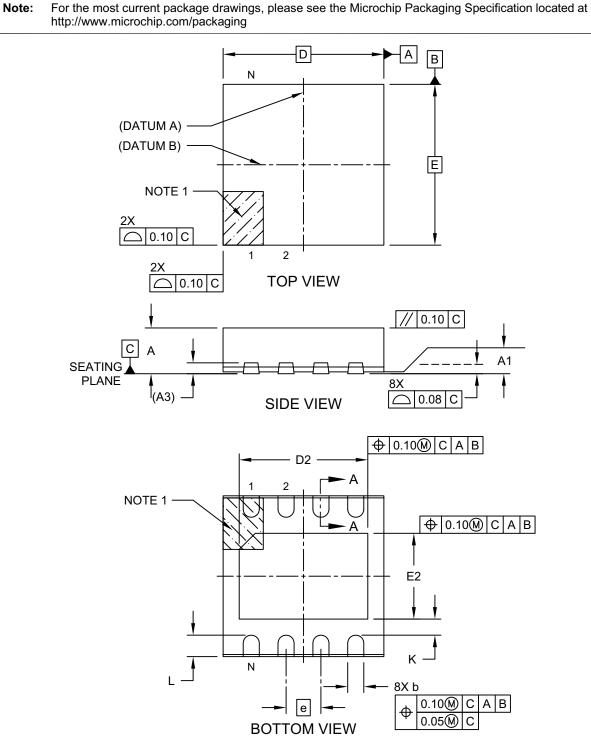
Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

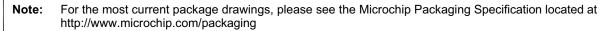
Microchip Technology Drawing C04-2057-SN Rev B

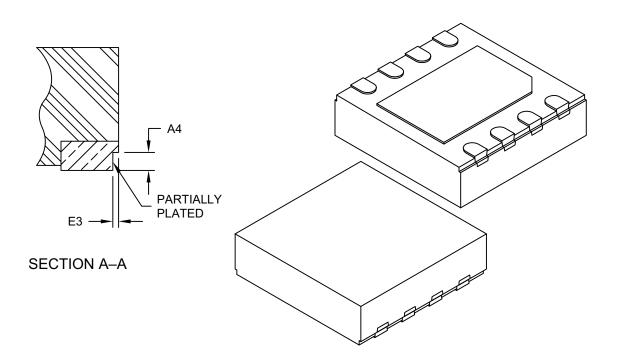
8-Lead Very Thin Plastic Dual Flat, No Lead Package (Q8B) - 3x3 mm Body [VDFN] With 2.40x1.60 mm Exposed Pad and Stepped Wettable Flanks



Microchip Technology Drawing C04-21358 Rev B Sheet 1 of 2

8-Lead Very Thin Plastic Dual Flat, No Lead Package (Q8B) - 3x3 mm Body [VDFN] With 2.40x1.60 mm Exposed Pad and Stepped Wettable Flanks





	MILLIMETERS					
Dimension	Limits	MIN	NOM	MAX		
Number of Terminals	N		8			
Pitch	е		0.65 BSC			
Overall Height	Α	0.80	0.85	0.90		
Standoff	A1	0.00	0.00 0.03			
Terminal Thickness	A3		0.203 REF			
Overall Length	D	3.00 BSC				
Exposed Pad Length	D2	2.30	2.30 2.40			
Overall Width	E		3.00 BSC			
Exposed Pad Width	E2	1.50	1.50 1.60			
Terminal Width	b	0.25	0.30	0.35		
Terminal Length	L	0.35	0.40	0.45		
Terminal-to-Exposed-Pad	K	0.20 -		-		
Wettable Flank Step Cut Depth	A4	0.10	0.13	0.15		
Wettable Flank Step Cut Width	E3	-	-	0.04		

Notes:

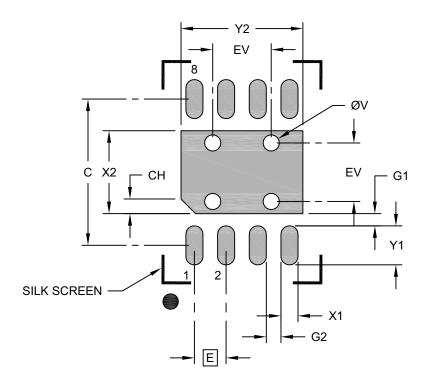
- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Package is saw singulated
- 3. Dimensioning and tolerancing per ASME Y14.5M
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-21358 Rev B Sheet 2 of 2

8-Lead Very Thin Plastic Dual Flat, No Lead Package (Q8B) - 3x3 mm Body [VDFN] With 2.40x1.60 mm Exposed Pad and Stepped Wettable Flanks

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	MILLIMETERS			
Dimension	MIN	NOM	MAX	
Contact Pitch	E	0.65 BSC		
Optional Center Pad Width	X2			1.70
Optional Center Pad Length	Y2			2.50
Contact Pad Spacing	С		3.00	
Contact Pad Width (X8)	X1			0.35
Contact Pad Length (X8)	Y1			0.80
Contact Pad to Center Pad (X8)	G1	0.20		
Contact Pad to Contact Pad (X6)	G2	0.20		
Pin 1 Index Chamfer	СН	0.20		
Thermal Via Diameter	V		0.33	
Thermal Via Pitch	EV		1.20	

Notes:

- 1. Dimensioning and tolerancing per ASME Y14.5M
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances.
- 2. For best soldering results, thermal vias, if used, should be filled or tented to avoid solder loss during reflow process

Microchip Technology Drawing C04-23358 Rev B

APPENDIX A: REVISION HISTORY

Revision D (August 2019)

The following is the list of modifications:

- 1. Updated TABLE 2-2: "Temperature Specifications".
- 2. Added test conditions at several parameters in TABLE 2-1: "Electrical Characteristics".

Revision C (September 2017)

The following is the list of modifications:

- 1. Added the Differential Receiver Threshold Voltage at recessive to Dominant transition parameter in Section 2.0, Electrical Characteristics.
- 2. Various typographical edits.

Revision B (July 2017)

The following is the list of modifications:

- 1. Added the new device ATA6566-GBQW0 and updated the related information across the document.
- 2. Updated Section "ATA6566 Family Members".
- 3. Corrected Section TABLE 2-1: "Electrical Characteristics".
- 4. Updated Section TABLE 2-2: "Temperature Specifications".
- 5. Updated the VDFN8 package drawing and added a Grade 0 package example to **Section 3.1, Package Marking Information**.
- 6. Added a ATA6566-GBQW0 example to the "Product Identification System" section.
- 7. Various typographical edits.

Revision A (June 2017)

• Original release of this document.

ATA6566

NOTES:

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

	vv		<u>[X]</u> ⁽¹⁾	X	Y	E	xampl	es:	
PART NO.	XX ackage	•	and Reel Option	A Package Directives Classification	Temperature Range	a)	ATA6	566-GAQW0:	ATA6566, 8-Lead SOIC, Tape and Reel package according to RoHS, Temperature Grade 0
Device:	ATA	6566	Star	n-Speed CAN Transceiv Idby Mode for the Japar I FD Ready		b)	ATA6	566-GBQW0:	ATA6566, 8-Lead VDFN, Tape and Reel package according to RoHS, Temperature Grade 0
Package:	GA GB		8-Lead SC 8-Lead VE			c)	ATA6	566-GAQW1:	ATA6566, 8-Lead SOIC, Tape and Reel package according to RoHS, Temperature Grade 1
Tape and Reel Option:	I Q	=	330 mm d	ameter Tape and Reel		d)	ATA6	566-GBQW1:	ATA6566, 8-Lead VDFN, Tape and Reel package according to RoHS, Temperature Grade 1
Package Directives Classification	w :	=	Package a	iccording to RoHS ⁽²⁾		No	ote 1:	catalog part num	dentifier only appears in the ber description. This identifier is g purposes and is not printed on
Temperature Range:	0 1	= =		re Grade 0 (-40°C to +1 re Grade 1 (-40°C to +1				the device packa	age. Check with your Microchip package availability with the
							2:	of 0.09% (900 p Chlorine (Cl) and total Bromine (B homogeneous n	r; maximum concentration value pm) for Bromine (Br) and d less than 0.15% (1500 ppm) r) and Chlorine (Cl) in any naterial. Maximum concentration 900 ppm) for Antimony (Sb) in us material.

ATA6566

NOTES:

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